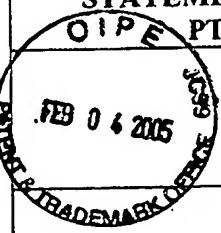


<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANTS</b> <b>PTO FORM 1449</b> 	<b>ATTY. DOCKET NO.</b> 10746/40	<b>SERIAL NO.</b> 10/775,806
	<b>APPLICANT(s)</b> S. KONDO et al.	
	<b>FILING DATE</b> 2/9/04	<b>GROUP</b> 2829 2891

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AKS	5,561,681	October 1, 1996	Nishimura TAKASHI			
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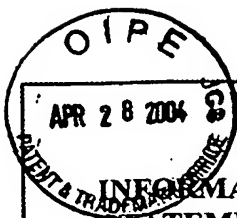
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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
						YES	NO
AKS	1 139 526	October 4, 2001	EP			English Document	

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>	ATTY. DOCKET NO. 10746/33A	U.S. SERIAL NO. 10/775,806
	APPLICANT(S) Susumu KONDO et al.	
	FILING DATE February 9, 2004	GROUP 2891 Not Yet Assigned

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	APPLICANT(S) Susumu KONDO et al.	
	FILING DATE February 9, 2004	GROUP <b>2891</b> Not Yet Assigned

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EXAMINER INITIAL	PATENT NUMBER	PATENT DATE	NAME	CLASS	SUBCLASS	FILING DATE

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